

8688

7

98

8688

9

8

5

8687

8687

8687

& /



2022 1 10

2020

5

10



%

%

%

&

+



& ,



9

#

#

#

9

/- . / . +

9

&

/

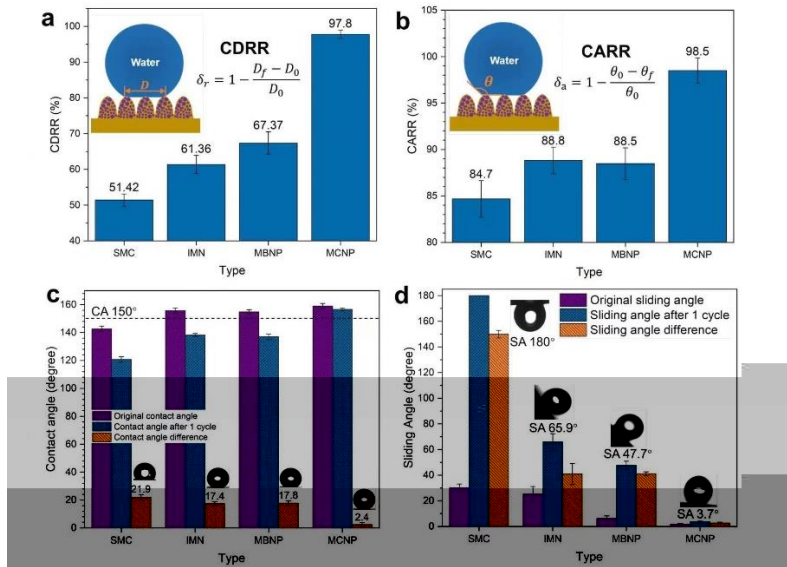
:

:

9

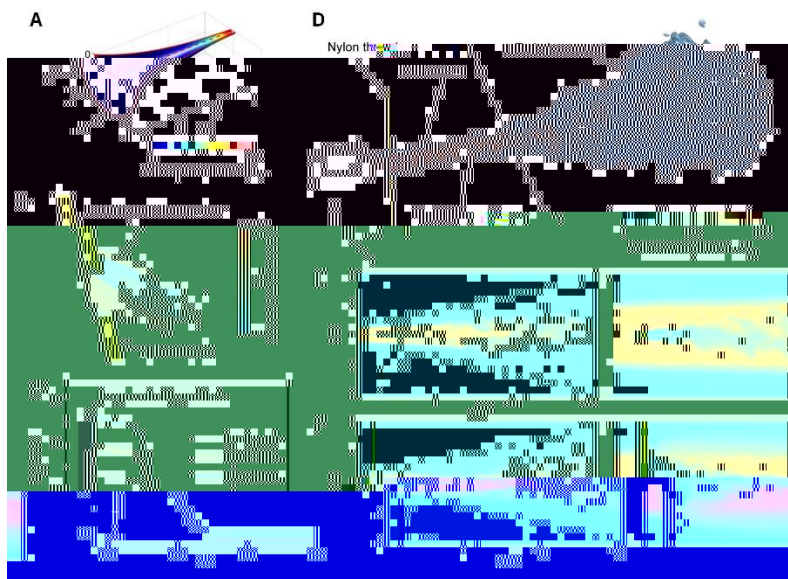
#

9



0

0% % % , -#& # . & , # #



7
% %& ,% ,/&

8

&&

9

"

8

The image displays a grid of scientific diagrams and plots illustrating various material engineering concepts:

- Substrate Engineering:** Shows a "Miscut Substrate" and an "Epitaxial Plane" with a diagram of a crystal lattice.
- Strain Engineering:** Illustrates strain states T, R, and O with corresponding 3D diagrams.
- Chemical Doping:** Shows two plots labeled FE and AFE, and a diagram of a crystal lattice with dopant atoms.
- Electric Boundary Conditions:** Shows "Open-circuit" and "Short-circuit" conditions with diagrams of layered structures.
- Solid Solutions:** Shows a diagram of a crystal lattice with dopant atoms and a plot labeled NFE.
- Domain Walls:** Shows diagrams of "Nanopatterned" and "Domain Walls" with a plot of "Magnetization" vs "Distance".
- Proximity Effects:** Shows diagrams of "Nano Islands", "Magnetic Islands", and "Proximity Effects" with a plot of "Magnetization" vs "Distance".

&

7 # # 9
0% %& &, % & &/

&

.
7 /.-
- //& 97
// # && &&

+&& && -/
#

9

8687

+ & &

+

,& + + /& / ++

9

+ & ,

8687

2021 12 30

A205

40



8687

1 4

A205

30



62784560

clx@tsinghua.edu.cn

C201